

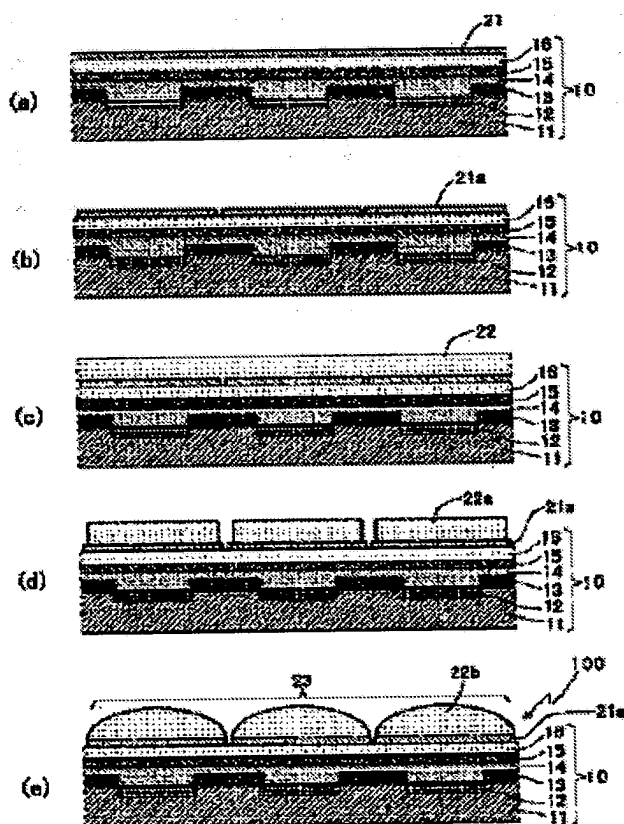
# SOLID-STATE IMAGE SENSING DEVICE MICROLENS ARRAY, SOLID- STATE IMAGE SENSING DEVICE PROVIDED WITH IT, AND METHOD OF MANUFACTURING THEM

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## Abstract of JP2000307090

**PROBLEM TO BE SOLVED:** To obtain a solid-state image sensing device microlens array and a solid-state image sensing device, where the photodetective part of a photoelectric conversion device is enhanced in photodetective efficiency, and a solid-state image sensing device can be improved in sensitivity and picture quality. **SOLUTION:** A photodetecting part 12, a light blocking part 13, a flattening layer 14, a color filter layer 15, and an overcoat layer 16 are formed on a semiconductor substrate 11 for the formation of a solid-state photoelectric conversion device 10, where a photosensitive base layer 21 is formed on the overcoat layer 16, subjected to patterning, and exposed to ultraviolet rays of wavelengths 350 nm or below to turn into a base pattern layer 21a. Furthermore, a lens forming layer 22 of photosensitive layer is formed, subject to patterning, and exposed to ultraviolet rays of wavelengths 350 to 400 nm to turn into a lens formation pattern layer 22a, the pattern layer 22a is made to flow by heating to turn into a microlens array 23 composed of microlenses 22b, and thus a solid-state image sensing device 100 is obtained.



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